

# NSS40300MZ4

## Bipolar Power Transistors 40 V, 3.0 A, Low $V_{CE(sat)}$ PNP Transistor

ON Semiconductor's e<sup>2</sup>PowerEdge family of low  $V_{CE(sat)}$  transistors are surface mount devices featuring ultra low saturation voltage ( $V_{CE(sat)}$ ) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e<sup>2</sup>PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

### Features

- Complement to NSS40301MZ4 Series
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	40	Vdc
Collector-Base Voltage	$V_{CB}$	40	Vdc
Emitter-Base Voltage	$V_{EB}$	6.0	Vdc
Base Current - Continuous	$I_B$	1.0	Adc
Collector Current - Continuous	$I_C$	3.0	Adc
Collector Current - Peak	$I_{CM}$	5.0	Adc
Total Power Dissipation Total $P_D$ @ $T_A = 25^\circ\text{C}$ (Note 1) Total $P_D$ @ $T_A = 25^\circ\text{C}$ (Note 2)	$P_D$	2.0 0.80	W
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

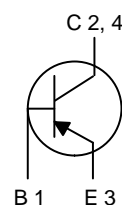
1. Mounted on 1" sq. (645 sq. mm) Collector pad on FR-4 bd material.
2. Mounted on 0.012" sq. (7.6 sq. mm) Collector pad on FR-4 bd material.



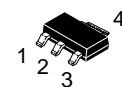
**ON Semiconductor**<sup>®</sup>

<http://onsemi.com>

**PNP TRANSISTOR  
3.0 AMPERES  
40 VOLTS, 2.0 WATTS**

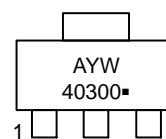


Schematic



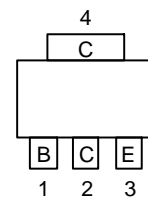
**SOT-223  
CASE 318E  
STYLE 1**

### MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- W = Work Week
- 40300 = Specific Device Code
- = Pb-Free Package

### PIN ASSIGNMENT



Top View Pinout

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

# NSS40300MZ4

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case Junction-to-Ambient on 1" sq. (645 sq. mm) Collector pad on FR-4 bd material Junction-to-Ambient on 0.012" sq. (7.6 sq. mm) Collector pad on FR-4 bd material	$R_{\theta JA}$ $R_{\theta JA}$	64 155	$^{\circ}C/W$
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	$T_L$	260	$^{\circ}C$

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector-Emitter Sustaining Voltage ( $I_C = 10$ mAdc, $I_B = 0$ Adc)	$V_{CEO(sus)}$	40	-	-	Vdc
Emitter-Base Voltage ( $I_E = 50$ $\mu$ Adc, $I_C = 0$ Adc)	$V_{EBO}$	6.0	-	-	Vdc
Collector Cutoff Current ( $V_{CB} = 40$ Vdc)	$I_{CBO}$	-	-	100	nAdc
Emitter Cutoff Current ( $V_{BE} = 6.0$ Vdc)	$I_{EBO}$	-	-	100	nAdc

### ON CHARACTERISTICS (Note 3)

Collector-Emitter Saturation Voltage ( $I_C = 0.5$ Adc, $I_B = 50$ mAdc) ( $I_C = 1.0$ Adc, $I_B = 20$ mAdc) ( $I_C = 3.0$ Adc, $I_B = 0.3$ Adc)	$V_{CE(sat)}$	-	-	0.070 0.150 0.400	Vdc
Base-Emitter Saturation Voltage ( $I_C = 1.0$ Adc, $I_B = 0.1$ Adc)	$V_{BE(sat)}$	-	-	1.0	Vdc
Base-Emitter On Voltage ( $I_C = 1.0$ Adc, $V_{CE} = 2.0$ Vdc)	$V_{BE(on)}$	-	-	0.9	Vdc
DC Current Gain ( $I_C = 0.5$ Adc, $V_{CE} = 1.0$ Vdc) ( $I_C = 1.0$ Adc, $V_{CE} = 1.0$ Vdc) ( $I_C = 3.0$ Adc, $V_{CE} = 1.0$ Vdc)	$h_{FE}$	200 175 100	- - -	- 350 -	-

### DYNAMIC CHARACTERISTICS

Output Capacitance ( $V_{CB} = 10$ Vdc, $f = 1.0$ MHz)	$C_{ob}$	-	40	-	pF
Input Capacitance ( $V_{EB} = 5.0$ Vdc, $f = 1.0$ MHz)	$C_{ib}$	-	130	-	pF
Current-Gain - Bandwidth Product (Note 4) ( $I_C = 500$ mA, $V_{CE} = 10$ V, $F_{test} = 1.0$ MHz)	$f_T$	-	160	-	MHz

3. Pulse Test: Pulse Width  $\leq 300$   $\mu$ s, Duty Cycle  $\leq 2\%$ .

4.  $f_T = |h_{FE}| \cdot f_{test}$

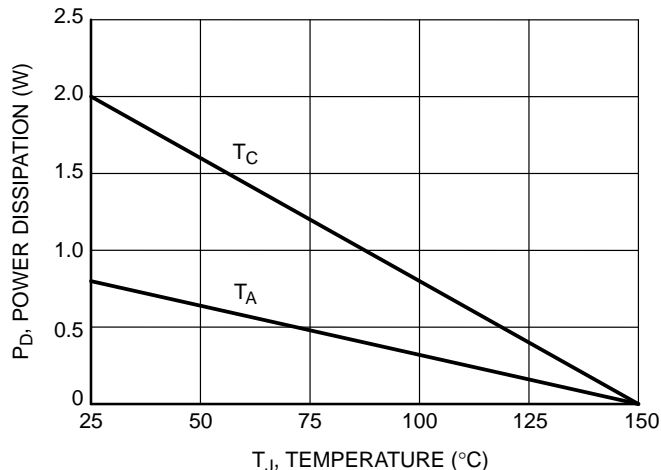


Figure 1. Power Derating

# NSS40300MZ4

## TYPICAL CHARACTERISTICS

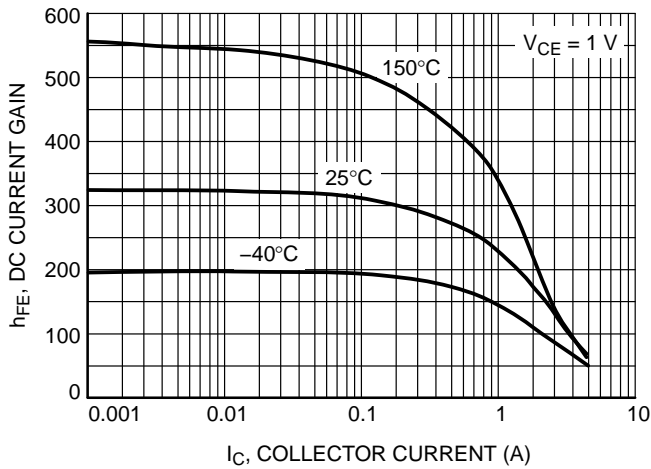


Figure 2. DC Current Gain

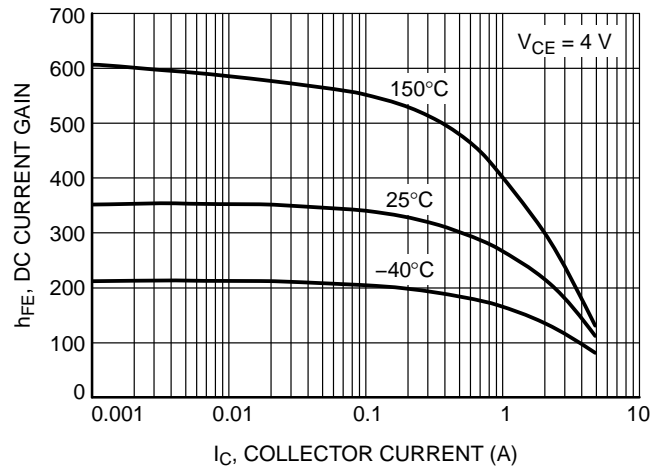


Figure 3. DC Current Gain

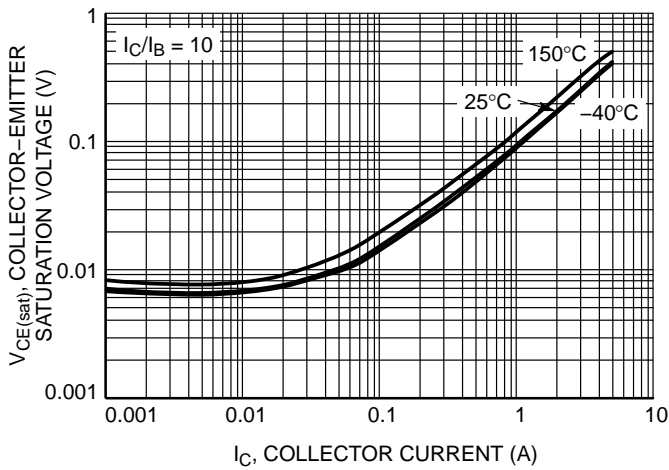


Figure 4. Collector-Emitter Saturation Voltage

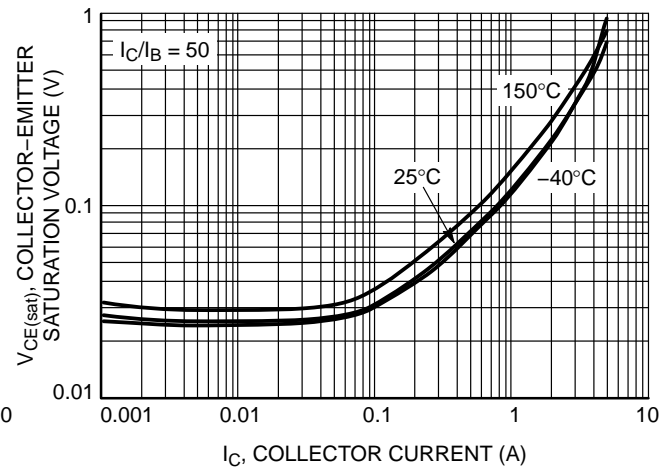


Figure 5. Collector-Emitter Saturation Voltage

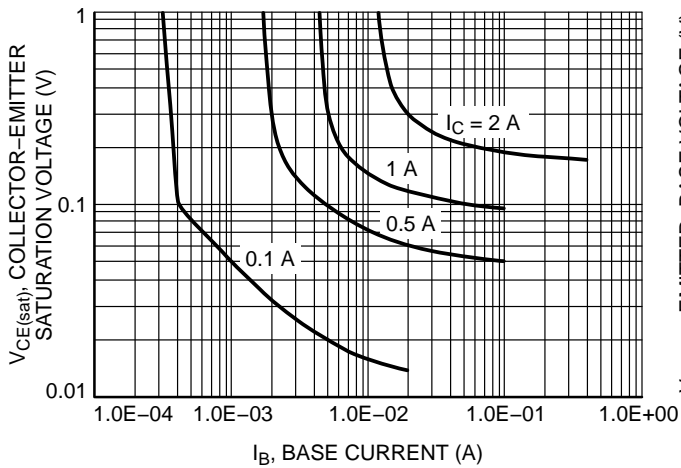


Figure 6. Collector Saturation Region

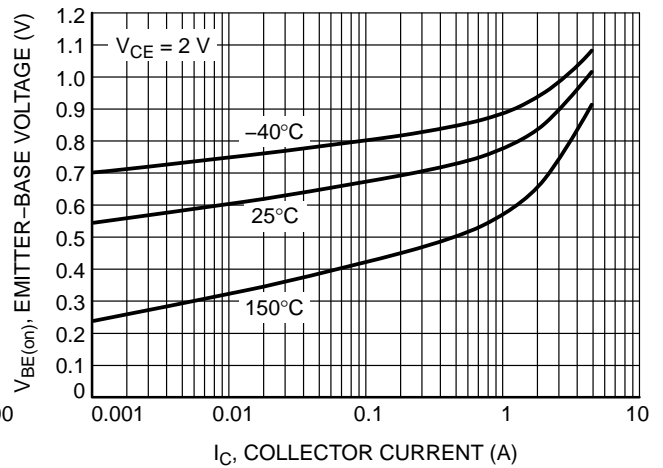


Figure 7.  $V_{BE(on)}$  Voltage

# NSS40300MZ4

## TYPICAL CHARACTERISTICS

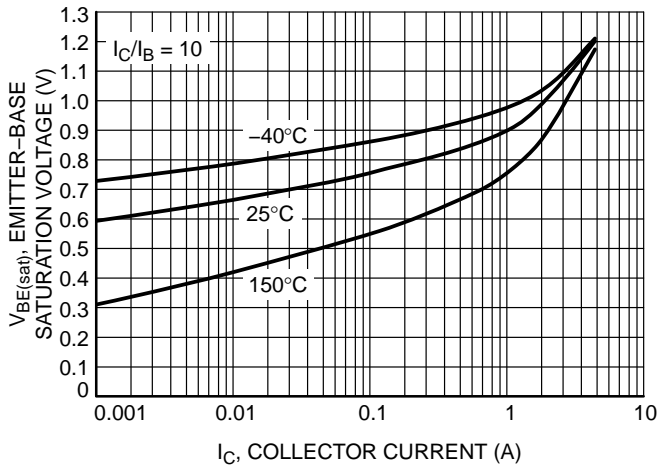


Figure 8. Base-Emitter Saturation Voltage

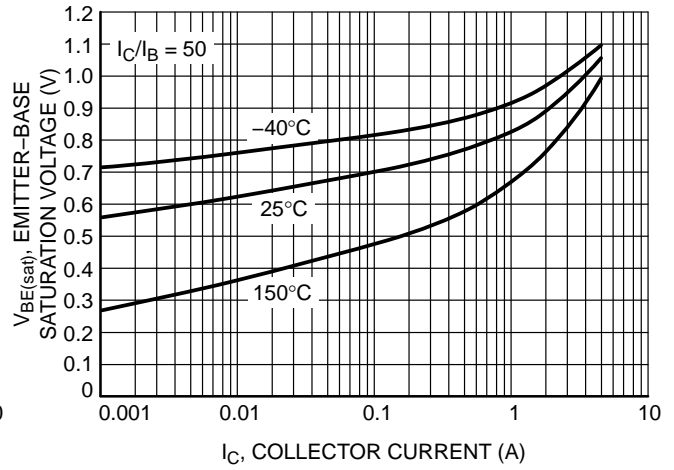


Figure 9. Base-Emitter Saturation Voltage

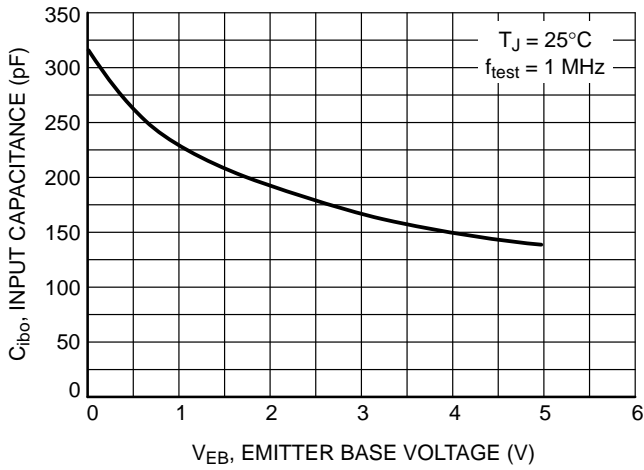


Figure 10. Input Capacitance

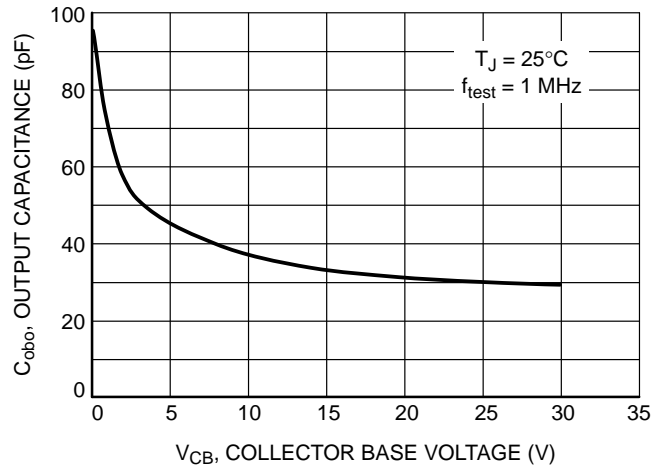


Figure 11. Output Capacitance

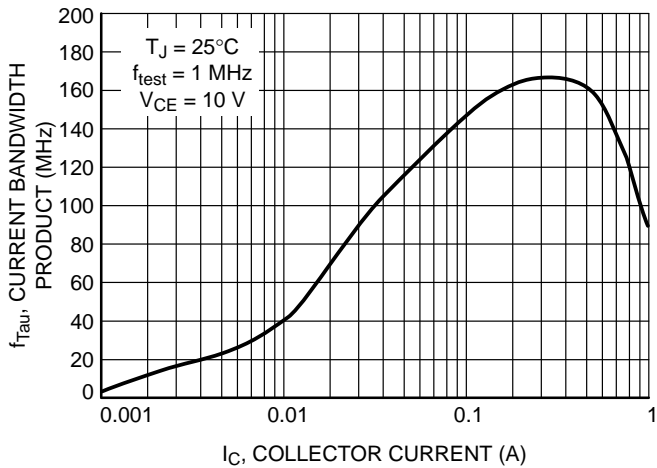


Figure 12. Current-Gain Bandwidth Product

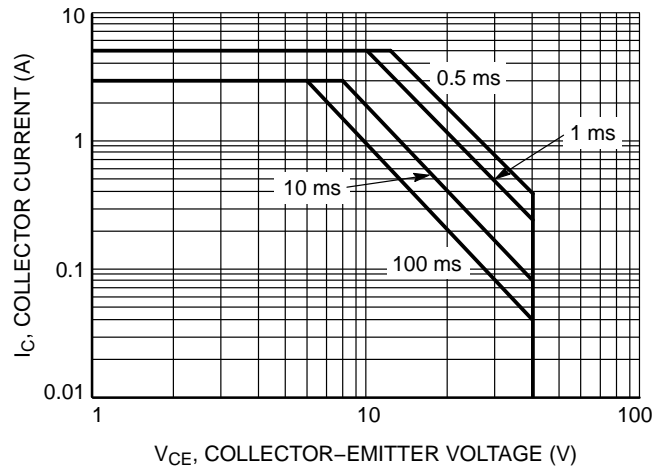


Figure 13. Safe Operating Area

# NSS40300MZ4

## ORDERING INFORMATION

Device	Package	Shipping†
NSS40300MZ4T1G	SOT-223 (Pb-Free)	1,000 / Tape & Reel
NSV40300MZ4T1G*	SOT-223 (Pb-Free)	1,000 / Tape & Reel
NSS40300MZ4T3G	SOT-223 (Pb-Free)	4,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 1:1

SOT-223 (TO-261)  
CASE 318E-04  
ISSUE R

DATE 02 OCT 2018



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
4. DATUMS A AND B ARE DETERMINED AT DATUM H.
5. A1 IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS b AND b1.

MILLIMETERS			
DIM	MIN.	NOM.	MAX.
A	1.50	1.63	1.75
A1	0.02	0.06	0.10
b	0.60	0.75	0.89
b1	2.90	3.06	3.20
c	0.24	0.29	0.35
D	6.30	6.50	6.70
E	3.30	3.50	3.70
e	2.30 BSC		
L	0.20	---	---
L1	1.50	1.75	2.00
He	6.70	7.00	7.30
$\theta$	0°	---	10°



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**SOT-223 (TO-261)**  
**CASE 318E-04**  
**ISSUE R**

DATE 02 OCT 2018

- |  |   |   |   |   |
|--|---|---|---|---|
| <b>STYLE 1:</b><br>PIN 1. BASE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR | <b>STYLE 2:</b><br>PIN 1. ANODE<br>2. CATHODE<br>3. NC<br>4. CATHODE        | <b>STYLE 3:</b><br>PIN 1. GATE<br>2. DRAIN<br>3. SOURCE<br>4. DRAIN           | <b>STYLE 4:</b><br>PIN 1. SOURCE<br>2. DRAIN<br>3. GATE<br>4. DRAIN   | <b>STYLE 5:</b><br>PIN 1. DRAIN<br>2. GATE<br>3. SOURCE<br>4. GATE    |
| <b>STYLE 6:</b><br>PIN 1. RETURN<br>2. INPUT<br>3. OUTPUT<br>4. INPUT        | <b>STYLE 7:</b><br>PIN 1. ANODE 1<br>2. CATHODE<br>3. ANODE 2<br>4. CATHODE | <b>STYLE 8:</b><br>CANCELLED  | <b>STYLE 9:</b><br>PIN 1. INPUT<br>2. GROUND<br>3. LOGIC<br>4. GROUND | <b>STYLE 10:</b><br>PIN 1. CATHODE<br>2. ANODE<br>3. GATE<br>4. ANODE |
| <b>STYLE 11:</b><br>PIN 1. MT 1<br>2. MT 2<br>3. GATE<br>4. MT 2             | <b>STYLE 12:</b><br>PIN 1. INPUT<br>2. OUTPUT<br>3. NC<br>4. OUTPUT         | <b>STYLE 13:</b><br>PIN 1. GATE<br>2. COLLECTOR<br>3. EMITTER<br>4. COLLECTOR |   |   |

**GENERIC  
 MARKING DIAGRAM\***



- A = Assembly Location
- Y = Year
- W = Work Week
- XXXXX = Specific Device Code
- = Pb-Free Package

(Note: Microdot may be in either location)  
 \*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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